L Number	Hits	Search Text	DB	Time stamp
1	5150	((257/57) or (257/59) or (257/66) or (257/66) or (257/72) or (257/347) or (257/350) or (313/513) or (445/25)).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/29 10:00
8	3	("5501011").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/29 07:37
15	2	("5501011" | "6265010").PN.	USPAT	2001/08/19 07:47
16	0	(("5501013" | "6046617").PN.) and organic with EL electroluminescence electroluminescent	USPAT	2001/08/19 07:46
17	0	(("5501013" | "6046617").PN.) and organic same EL electroluminescence electroluminescent	USPAT	2001/08/19 07:46
18	3	semiconductor-energy-laboratory.as.	USPAT	2001/08/19 07:48
19	4	semiconductor-energy-laboratory.as.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/08/19 07:51
26	7	s.ny.as. and single adj crystal and active adj matrix and gate with (FET field adj effect adj transistor)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/08/19 07:55
33	2	s.ny.as. and single adj crystal and active adj matrix and gate with (FET field adj effect adj transistor) and (organic with (EL electroluminescent electroluminescence))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/08/19 08:00
40	0	s.ny.as. and single adj crystal and active adj matrix and gate with (FET field adj effect adj transistor) and (organic with (EL electroluminescent electroluminescence)) and inert	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/08/19 08:00
47	2	((((257/57) or (257/59) or (257/66) or (257/66) or (257/72) or (257/347) or (257/350) or (313/513) or (445/25)).CCLS.) and active adj matrix and organic with EL and gate with (field adj effect adj transistor FET) and single adj crystal	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/08/19 08:38
54	2	((((257/57) or (257/59) or (257/66) or (257/66) or (257/72) or (257/347) or (257/350) or (313/513) or (445/25)).CCLS.) and active adj matrix and (organic with EL electroluminescence electroluminescent) and gate with (field adj effect adj transistor FET) and single adj crystal	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/08/29 08:43
61	8	(((257/57) or (257/59) or (257/66) or (257/66) or (257/72) or (257/347) or (257/350) or (313/513) or (445/25)).CCLS.) and active adj matrix and (organic with (EL electroluminescence electroluminescent) and gate with (field adj effect adj transistor FET bottom adj gate top adj gate) and single adj crystal	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/08/29 08:44
68	8	(((257/57) or (257/59) or (257/66) or (257/72) or (257/72) or (257/347) or (257/350) or (313/512) or (445/25)).CCLS.) and active adj matrix and organic with (EL electroluminescence electroluminescent) and gate with (field adj effect adj transistor FET bottom adj gate top adj gate) and single adj crystal and gas	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/29 08:44

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75	5	(((257/57) or (257/59) or (257/76) or (257/... or (257/...) or (257/...) or (25... or (31.../612) or (44.../15)).CCLS.) and active adj matrix and (organic with (EL electroluminescence electro luminescent)) and gate with (field adj effect adj transistor FET bottom adj gate top adj gate) and single adj crystal and inert adj gas)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/29 10:17
82	80	(((257/57) or (257/59) or (257/76) or (257/... or (257/...) or (257/...) or (257/...) or (31.../...) or (44/15)).CCLS.) and TFT with FET	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/29 09:25
89	1	6274... .UREPN.	USPAT	2002/08/29 09:55
90	14	("..." | "..." | "..." | "5714..." | "5412..." | "..." | "54..." | "5710..." | "5714045" | "573..." | "575..." | "5913..." | "5912729" | "5...").PN.	USPAT	2002/08/29 09:56
91	0	("..." | "..." | "..." | "5576..." | "5411834" | "5430..." | "5...." | "571..." | "671..." | "5..." | "5..." | "552..." | "5...." | "5....").PN.) and active adj matrix and (organic with (EL electroluminescence electroluminescent)) and gate with (field adj effect adj transistor FET bottom adj gate top adj gate) and single adj crystal and (inert adj gas)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/29 09:59
98	0	("..." | "..." | "5411982" | "5...." | "5412..." | "542...05" | "5...." | "5710608" | "5713005" | "573..." | "5...." | "5413942" | "5912735" | "5....").PN.) and active adj matrix and (organic with (EL electroluminescence electroluminescent)) and gate and single adj crystal and (inert adj gas)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/29 09:59
105	492	((257/57) or (257/59) or (257/76) or (257/66) or (257/71) or (257/347) or (257/350) or (313/512) or (446/25)).CCLS.) and inert gas with organic adj EL	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/29 10:02
112	9	(((257/57) or (257/59) or (257/66) or (257/...) or (257/71) or (257/347) or (257/350) or (313/512) or (445/15)).CCLS.) and inert adj gas with organic adj EL	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/29 10:02
119	0	(((257/57) or (257/59) or (257/66) or (257/66) or (257/71) or (257/347) or (257/...) or (313/...) or (445/15)).CCLS.) and inert adj gas with organic adj EL same oxidize	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/29 10:03
126	0	(((257/57) or (257/59) or (257/66) or (257/71) or (257/...) or (44/15)).CCLS.) and inert adj gas same organic adj EL same oxidize deteriorate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/29 10:03
133	0	(((257/57) or (257/59) or (257/76) or (257/... or (257/72) or (257/347) or (257/350) or (313/512) or (44/15).CCLS.) and active adj matrix and (organic with EL electroluminescence electroluminescent)) and gate with (field adj effect adj transistor FET bottom adj gate top adj gate) and single adj crystal and (rare adj gas)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/29 10:20

140	6	(((257/57) or (257/59) or (257/66) or (257/6_ or (257/72) or (257/3)) or (257/_)) or (313/512) or (445/_).CCLS.) and active adj matrix and (organic with (EL electroluminescen e electroluminescent)) and gate with (field adj effect adj transistor FET bottom adj gate t_ adj gate) and single adj crystal and (helium he argon ar krypton kr xenon xe nitrogen n))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/29 10:21
147	3	(((257/57 or (257/59 or 257/66 or (257/6_ or (257/7_ or (257/34) or (257/35)) or 313/512 or (445/21).CCLS.) and active adj matrix and (organic with (EL electroluminescence electroluminescent)) and gate with (field adj effect adj transistor FET bottom adj gate top adj gate) and single adj crystal and (helium he argon ar krypton kr xenon xe nitrogen n))	USPAT; EPO; JPO; DERWENT; IBM_TDB	2002/08/29 10:24
153	3	(((257/57) or (257/59) or (257/66) or (257/6_ or (257/7_ or (257/34) or (257/35)) or (313/512) or (445/ _).CCLS.) and active adj matrix and (organic with (EL electroluminescence electroluminescent)) and gate with (field adj effect adj transistor FET bottom adj gate top adj gate) and single adj crystal	USPAT; EPO; JPO; DERWENT; IBM_TDB	2002/08/29 11:12
159	3	(((257/57) or (257/59) or (257/66) or (257/6_ or (257/7_ or (257/34) or (257/35)) or (313/512) or (445/21).CCLS.) and active adj matrix and (organic with (EL electroluminescence electroluminescent)) and gate with (field adj effect adj transistor FET bottom adj gate top adj gate) and single adj crystal) and (helium he argon ar krypton kr xenon xe nitrogen n))	USPAT; EPO; JPO; DERWENT; IBM_TDB	2002/08/29 10:26
165	3	((((257/57) or (257/59) or (257/66) or (257/6_ or (257/72) or (257/34) or (257/35)) or (313/512) or (445/21).CCLS.) and active adj matrix and (organic with (EL electroluminescence electroluminescent)) and gate with (field adj effect adj transistor FET bottom adj gate top adj gate) and single adj crystal) and (helium he argon ar krypton kr xenon xe nitrogen n))	USPAT; EPO; JPO; DERWENT; IBM_TDB	2002/08/29 10:27
171	1	(((257/57) or (257/59) or (257/66) or (257/6_ or (257/7_ or (257/34) or (257/35)) or (313/512) or (445/5_).CCLS.) and active adj matrix and (organic with (EL electroluminescence electroluminescent)) and gate with (field adj effect adj transistor FET bottom adj gate top adj gate) and single adj crystal) and (helium he argon ar krypton kr xenon xe nitrogen n) and (barium adj oxide silica adj gel drying))	USPAT; EPO; JPO; DERWENT; IBM_TDB	2002/08/29 10:28
177	1	((((257/57) or (257/59) or (257/66) or (257/6_ or (257/7_ or (257/34) or (257/35)) or (313/512) or (445/15).CCLS.) and active adj matrix and (organic with (EL electroluminescence electroluminescent)) and gate with (field adj effect adj transistor FET bottom adj gate top adj gate) and single adj crystal and (helium he argon ar krypton kr xenon xe nitrogen n)) and (helium he argon ar krypton kr xenon xe nitrogen n) and (barium adj oxide silica adj gel drying)	USPAT; EPO; JPO; DERWENT; IBM_TDB	2002/08/29 10:28

183	1	((((257/57) or (257/59) or (257/66) or (25...66) or 257/72 or (257/347) or (25...350) or (313...512) or (445/25)).CCLS.) and active adj matrix and (organic with (EL electroluminescence electroluminescent)) and gate with (field adj effect adj transistor FET bottom adj gate top adj gate) and single adj crystal and (helium he argon ar krypton kr xenon xe nitrogen ni) and (helium he argon ar krypton or xenon xe nitrogen n inert adj gas inert adj gas) and (barium adj oxide silica adj gel drying)	USPAT; EPO; JPO; DERWENT; IBM_TDB	2002/08/29 10:29
189	1	((((257/57) or (257/59) or (257/66) or (257/66) or (257/72) or (257/347) or (257/350) or (313/512) or (445/25)).CCLS.) and active adj matrix and (organic with (EL electroluminescence electroluminescent)) and gate with (field adj effect adj transistor FET bottom adj gate top adj gate) and single adj crystal and (helium he argon ar krypton kr xenon xe nitrogen ni) and (helium he argon ar krypton or xenon xe nitrogen n inert adj gas rare adj gas) and (barium adj oxide silica adj gel drying)	USPAT; EPO; JPO; DERWENT; IBM_TDB	2002/08/29 11:14
195	4	((((257/57) or (257/59) or (257/66) or (257/66) or (257/72) or (257/347) or (257/350) or (313/512) or (445/25)).CCLS.) and active adj matrix and (organic with (EL electroluminescence electroluminescent)) and (field adj effect adj transistor FET bottom adj gate top adj gate) and single adj crystal	USPAT; EPO; JPO; DERWENT; IBM_TDB	2002/08/29 11:20
201	1	((((257/57) or (257/59) or (257/66) or (257/66) or (257/72) or (257/347) or (257/350) or (313/512) or (445/25)).CCLS.) and active adj matrix and (organic with (EL electroluminescence electroluminescent)) and (field adj effect adj transistor FET bottom adj gate top adj gate) and single adj crystal and (helium he argon ar krypton kr xenon xe nitrogen n inert adj gas rare adj gas) and (barium adj oxide silica adj gel drying)	USPAT; EPO; JPO; DERWENT; IBM_TDB	2002/08/29 11:15
207	4	((((257/57) or (257/59) or (257/66) or (257/66) or (257/72) or (257/347) or (257/350) or (313/512) or (445/25)).CCLS.) and matrix and (organic with (EL electroluminescence electroluminescent)) and (field adj effect adj transistor FET bottom adj gate top adj gate) and single adj crystal	USPAT; EPO; JPO; DERWENT; IBM_TDB	2002/08/29 11:21
–	229	(445/25).CCLS.	USPAT	2002/08/28 14:30
–	343	(313/512).CCLS.	USPAT	2002/08/28 14:39
–	0	"6374274".ap.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/28 14:39
–	1	"6374274".ap.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/28 14:39
–	229	(445/25).CCLS.	USPAT	2002/08/28 14:48
–	722	(313/512 or 445/25).CCLS.	USPAT; EPO; JPO; DERWENT; IBM_TDB	2002/08/28 14:48

17	(((313/512) or (445/25)).CCLS.) and active adj matrix	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/28 14:55
13	(((((313/512) or (445/25)).CCLS.) and active adj matrix) and crystal	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/28 14:56
1	(((((313/512) or (445/25)).CCLS.) and active adj matrix) and single adj crystal	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/28 14:58
3	5672.88.UREN.	USPAT	2002/08/28 14:57
1	(((313/512) or (445/25)).CCLS.) and active adj matrix) and (field adj effect adj transistor FET)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/28 15:01
0	(257.$).ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/28 15:01
134751	(257/$..ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/28 15:02
66945	(313/$).ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/28 15:02
8	((257/$).ccls.) and active adj matrix and (organic with EL) and gate with (field adj effect adj transistor FET)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/28 15:04
5	((257/$).ccls.) and active adj matrix and (organic with EL) and gate with (field adj effect adj transistor FET) and single adj crystal	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/28 15:32
0	((313/$).ccls.) and active adj matrix and (organic with EL) and gate with (field adj effect adj transistor FET) and single adj crystal	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/28 15:25
4347	((257/57) or (257/59) or (257/66) or (257/66) or (257/72) or (257/347) or (257/350)).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/28 16:14
2	(((257/57) or (257/59) or (257/66) or (257/66) or (257/72) or (257/347) or (257/350)).CCLS.) and active adj matrix and (organic with EL) and gate with (field adj effect adj transistor FET) and single adj crystal	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/29 08:36
4396	yamazaki-shunpei.in. or arai-yasuyuki.in.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/28 15:31

4178 yamazaki-shunpei.in.   USPAT;   2002/08/28 15:31
                                                             US-PGPUB;
                                                             EPO; JPO;
                                                             DERWENT;
                                                             IBM_TDB

943 yamazaki-shunpei.in. or arai-yasuyuki.in.   USPAT   2002/08/28 15:32
1171 yamazaki-shunpei.in. or arai-yasuyuki.in.   USPAT;   2002/08/28 15:32
                                                             US-PGPUB

0 (yamazaki-shunpei.in. or   USPAT;   2002/08/28 15:33
   arai-yasuyuki.in.) and active adj matrix   US-PGPUB;
   and (organic with EL) and gate with (field   EPO; JPO;
   adj effect adj transistor FET) and single   DERWENT;
   adj crystal   IBM_TDB
1 (yamazaki-shunpei.in. or   USPAT;   2002/08/28 15:33
   arai-yasuyuki.in.) and active adj matrix   US-PGPUB;
   and (organic with EL) and gate with (field   EPO; JPO;
   adj effect adj transistor FET) and single   DERWENT;
   adj crystal   IBM_TDB
3 1039595.URPN.   USPAT   2002/08/28 15:35
2 (((257/57) or (257/59) or (257/66) or   USPAT;   2002/08/28 16:15
   (257/66) or (257/72) or (257/347) or   US-PGPUB;
   (257/350)).CCLS.) and active adj matrix   EPO; JPO;
   and (organic with EL) and gate with (field   DERWENT;
   adj effect adj transistor FET mostft) and   IBM_TDB
   single adj crystal
5136 ((257/57) or (257/59) or (257/66) or   USPAT;   2002/08/29 07:37
   (257/66) or (257/72) or (257/347) or   US-PGPUB;
   (257/350) or (313/512) or (445/25)).CCLS.   EPO; JPO;
                                                             DERWENT;
                                                             IBM_TDB

2 (((257/57) or (257/59) or (257/66) or   USPAT;   2002/08/28 16:15
   (257/66) or (257/72) or (257/347) or   US-PGPUB;
   (257/350) or (313/512) or (445/25)).CCLS.)   EPO; JPO;
   and active adj matrix and (organic with   DERWENT;
   EL) and gate with (field adj effect adj   IBM_TDB
   transistor FET mostft) and single adj
   crystal
2 ("6153893" | "6246070").PN.   USPAT   2002/08/28 16:27